



CRT-1100S

Fotocellula anti-cavallotto range 1100mt Overlapping Photocell range 1100mt









Specifications for Amplifier

Built-in Photoelectric Sensor Long Distance Thru-Beam Type

Item	Description			
Power Source	12 to 24V ±10%, Ripple P-P: 10% or less			
Current Consumption	70 mA or less (Emitter and Receiver)			
Response Time	5 ms or less			
Modulation Method	Pulse Modulation System			
Output Ratings	Output Method: NPN transistor output with pull-up resister			
	Max. Sink Current: 80 mA			
	Impedance: Transistor ON when sensor is in ON state			
	Voltage: 1 V or less when sensor is ON state. and (Power Voltage -1.5V)			
	or more when sensor is OFF state			
Output Operation Mode	Black Lead Wire: Light-ON			
	White Lead Wire: Dark-ON			
	Emitter: Power Red LED			
Operation Indicator	Receiver:Output Red LED			
	Status Green LED			
Light Emitting Element	Infrared LED			
Light Receiving Element	Silicon Photo Diode			
Extraneous Light	Sunlight: 11000 lx (illuminance on light receiving plane Incandescent			
Immunity	Lamp: 3500 lx (illuminance on light receiving plane)			
Sensing Distance	1100 mt			
Sensing Object	Opaque object			
Vibration	IEC 60947-5-2, part 7.4.2Ø			
Mechanical Shock	IEC 60947-5-2, part 7.4.1			
Withstand				
Operating temperature	-10 to +60°C			
Ambient Humidity	35 to 85% RH			
Enclosure Protection	IP65			
Mechanical Specifications	Nickel plated brass Lens: Glass			
	PVC Cable, grey 2m OD 5.0 mm, ID: 42x0.1x2C			
Cable	our ead res		Receiver	Emitter
	Cole of L	Brown	+V	+V
		Black	Output(Light-ON)	
		Blue	0V	0V
Weight	Approx, 992 g (A set of Emitter and Receiver)			
Dimensions	54(W)x54(H)x112,2(L)			
	Emitter Receiver			
Output Circuit	Image: Second constraints D1 +V (Brown) Image: Second constraints Image: Second constraints Image: Second constraints Image: Second constraints Image: Second constraints Image: Second constraints Image: Second constraints Image: Second constraints Image: Second constraints Image: Second constraints </th			

